

1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-30612

2. Structure :

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :
Top side : Aluminum Alloy
Back side : Gold Layer.

3. Size :

- 3-1. ^{**1}Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm).
 - 3-2. Chip thickness : 3.3 ± 0.6 mils (0.085 ± 0.015 mm)
 - 3-3. Active area : 4.1 mils x 4.1 mils (0.105 mm x 0.105 mm).
 - 3-4. Bonding pad : 4.5 mils x 4.5 mils (0.115 mm x 0.115 mm).
 - 3-5. Pattern drawing : Refer to the attached drawing.
- ^{**1}Including scribing line. The chip size is about $(0.155 \pm 0.015)^2 \text{mm}^2$ after dicing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	$V_R=9V$ $E_e=0\text{mW}/\text{cm}^2$			100	nA
Zener Voltage	V_z	$I_z=5\text{mA}$ $E_e=0\text{mW}/\text{cm}^2$	10	12	14	V
Forward Voltage	V_f	$I_f=20\text{mA}$ $E_e=0\text{mW}/\text{cm}^2$	750		1200	mV

